

## AMENDMENTS TO THE CLAIMS

Claim 1 (currently amended) A method for producing bulk micromachined devices for use in Microelectromechanical Systems (MEMS), comprising the steps of:

providing a crystalline wafer with a front plane,

processing from said wafer at least one bulk micromachined device comprising at least one elongated opening or cavity, the opening or cavity having a longitudinal axis, so that an angle is formed by said longitudinal axis and a line formed by intersection of the front plane of the wafer and a first cleavage plane, said first cleavage plane being defined as a plane along which cleavage of the wafer is most-likely to occur, wherein said longitudinal axis is not parallel with a second cleavage plane, said second cleavage plane also being defined as a plane along which cleavage is likely to occur.

Claim 2 (currently amended) A method according to claim 1, wherein said wafer has a shape of a circular disc, with ~~at least one~~ or more part-parts cut off along ~~a one or more chord~~ chords of said circular disc, the longest of said chords being a flat of said wafer.

Claim 3 (original) A method according to claim 2 wherein said flat is not parallel to ~~said the intersection of said front plane with said first cleavage plane.~~

Claim 4 (original) A method according to claim 2, wherein said flat is parallel to ~~said the intersection of said front plane with said first cleavage plane.~~

Claim 5 (original) A method according to claim 4,  
wherein said wafer has a back plane,  
wherein said wafer is a silicon wafer, whose front and back planes are oriented along a  
plane of the {100} family, and  
wherein said cleavage plane is a plane belonging to the {111} family.

Claim 6 (original) A method according to claim 5, wherein said angle is less than  
45°.

Claim 7 (original) A method according to claim 4, wherein said wafer is a silicon  
wafer, whose front and back surfaces are oriented along a plane of the {100} family and wherein  
said cleavage plane is a plane belonging to the {110} family.

Claim 8 (original) A method according to claim 7, wherein said angle is less than  
45°.

Claim 9 (original) A method according to claim 4, wherein said processing  
comprises the steps of:

subjecting said wafer to a photolithography step, whereby a pattern is printed through a  
mask onto said wafer; and

etching said wafer,

characterised in that said photolithography step comprises the step of rotating said mask  
over an angle with respect to said wafer.

Claim 10 (original) A method according to claim 9, wherein said photolithography step comprises a contact printing step.

Claim 11 (original) A method according to claim 9, wherein said photolithography step comprises a proximity printing step.

Claim 12 (original) A method according to claim 4, wherein said processing comprises the steps of:

subjecting said wafer to a photolithography step, whereby a pattern is printed through a mask onto said wafer;

etching said wafer,

wherein said pattern is positioned at an angle with respect to said mask.

Claim 13 (original) A method according to claim 12, wherein said photolithography step comprises a contact printing step.

Claim 14 (original) A method according to claim 12, wherein said photolithography step comprises a proximity printing step.

Claim 15 (original) A method according to claim 4, wherein said processing comprises the steps of:

subjecting said wafer to a photolithography step, whereby a pattern is printed through a mask onto said wafer;

etching said wafer,  
characterised in that said photolithography step comprises the step of rotating said wafer over an angle with respect to said mask.

Claim 16 (original) A method according to claim 15, wherein said photolithography step comprises a contact printing step.

Claim 17 (original) A method according to any claim 15, wherein said photolithography step comprises a proximity printing step.

Claim 18 (original) A method according to claim 3, wherein said processing comprises the steps of:

subjecting said wafer to a photolithography step, whereby a pattern is printed through a mask onto said wafer,

etching said wafer.

Claim 19 (original) A method according to claim 18, wherein said photolithography step comprises a number of projection printing steps.

Claim 20 (original) A method according to claim 18, wherein said photolithography step comprises a contact printing step.

Claim 21 (original) A method according to claim 18, wherein said photolithography step comprises a proximity printing step.

Claim 22 (original) A micromachined device for use in Microelectromechanical Systems, said device being produced according to the method described in claim 1.

Claim 23 (original) Use of a micromachined device in Microelectromechanical Systems, said device being produced according to the method described in claim 1.